

BC846BS

65 V, 100 mA NPN/NPN general-purpose transistor

Rev. 01 — 24 August 2009

Product data sheet

1. Product profile

1.1 General description

NPN/NPN general-purpose transistor pair in a very small Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package		PNP/PNP	NPN/PNP
	Nexperia	JEITA	complement	complement
BC846BS	SOT363	SC-88	BC856BS	BC846BPN

1.2 Features

- Low collector capacitance
- Low collector-emitter saturation voltage
- Closely matched current gain
- Reduces number of components and board space
- No mutual interference between the transistors
- AEC-Q101 qualified

1.3 Applications

■ General-purpose switching and amplification

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transistor						
V_{CEO}	collector-emitter voltage	open base	-	-	65	V
I _C	collector current		-	-	100	mA
h _{FE}	DC current gain	V_{CE} = 5 V; I_{C} = 2 mA	200	300	450	



65 V, 100 mA NPN/NPN general-purpose transistor

2. Pinning information

Table 3. Pinning

Table 5.	i iiiiiiig		
Pin	Description	Simplified outline	Graphic symbol
1	emitter TR1	D- D- D.	2 5 4
2	base TR1	<u> </u>	6 5 4
3	collector TR2		TR2
4	emitter TR2	0	(TR1)
5	base TR2	□1 □2 □3	
6	collector TR1		1 2 3
			sym020

3. Ordering information

Table 4. Ordering information

Type number	Package	Package		
	Name	Description	Version	
BC846BS	SC-88	plastic surface-mounted package; 6 leads	SOT363	

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
BC846BS	*E5

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

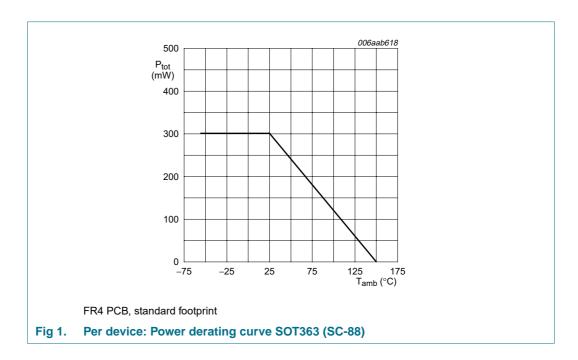
Symbol	Parameter	Conditions	Min	Max	Unit
Per transiste	or				
V_{CBO}	collector-base voltage	open emitter	-	80	V
V_{CEO}	collector-emitter voltage	open base	-	65	V
V_{EBO}	emitter-base voltage	open collector	-	6	V
I _C	collector current		-	100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
I _{BM}	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] _	200	mW

65 V, 100 mA NPN/NPN general-purpose transistor

Table 6. Limiting values ...continued In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per device					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	<u>[1]</u> _	300	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



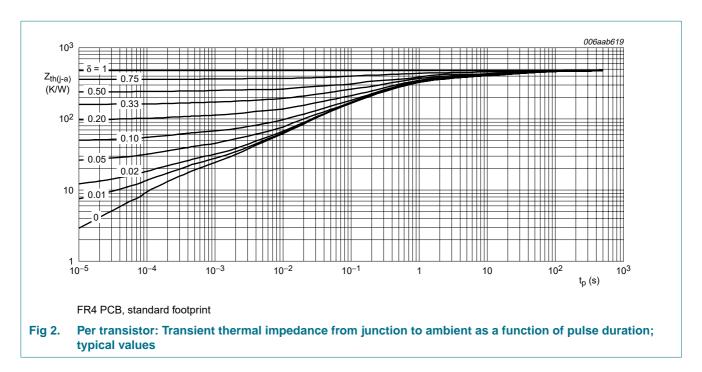
6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	625	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	230	K/W
Per device	•					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	416	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

65 V, 100 mA NPN/NPN general-purpose transistor



7. Characteristics

Table 8. Characteristics

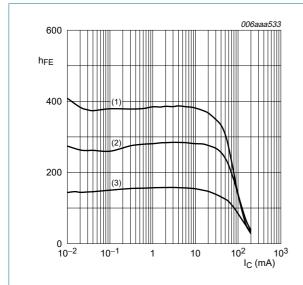
 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor					
I _{CBO} collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_{E} = 0 \text{ A}$	_	-	15	nA	
	$V_{CB} = 30 \text{ V; } I_E = 0 \text{ A;}$ $T_j = 150 ^{\circ}\text{C}$	-	-	5	μΑ	
I _{EBO}	emitter-base cut-off current	$V_{EB} = 6 \text{ V}; I_{C} = 0 \text{ A}$	-	-	100	nA
h _{FE} DC current gain		V _{CE} = 5 V				
	I _C = 10 μA	-	280	-		
		I _C = 2 mA	200	300	450	
V _{CEsat}	collector-emitter	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	55	100	mV
	saturation voltage	I _C = 100 mA; I _B = 5 mA	-	200	300	mV
V_{BEsat}	base-emitter	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	755	850	mV
	saturation voltage	I _C = 100 mA; I _B = 5 mA	-	1000	-	mV
V _{BE} base-emitter volta		V _{CE} = 5 V				
		I _C = 2 mA	580	650	700	mV
		I _C = 10 mA	-	-	770	mV

65 V, 100 mA NPN/NPN general-purpose transistor

Table 8. Characteristics ... continued $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0 \text{ A};$ f = 1 MHz	-	1.9	-	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_C = I_c = 0 \text{ A};$ f = 1 MHz	-	11	-	pF
f _T	transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz	100	-	-	MHz
NF	noise figure	V_{CE} = 5 V; I_{C} = 0.2 mA; R_{S} = 2 k Ω ; f = 10 Hz to 15.7 kHz	-	1.9	-	dB
		V_{CE} = 5 V; I_{C} = 0.2 mA; R_{S} = 2 k Ω ; f = 1 kHz; B = 200 Hz	-	3.1	-	dB



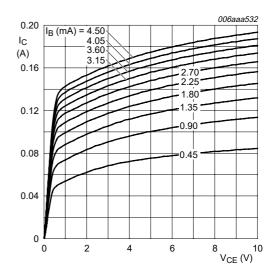
 $V_{CE} = 5 V$

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) $T_{amb} = -55 \, ^{\circ}C$

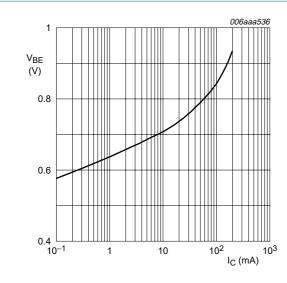
Fig 3. Per transistor: DC current gain as a function of collector current; typical values



 T_{amb} = 25 $^{\circ}C$

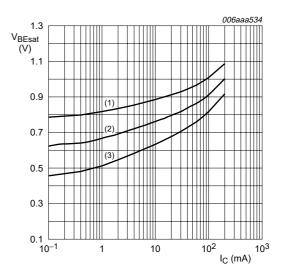
Fig 4. Per transistor: Collector current as a function of collector-emitter voltage; typical values

65 V, 100 mA NPN/NPN general-purpose transistor



V_{CE} = 5 V; T_{amb} = 25 °C

Fig 5. Per transistor: Base-emitter voltage as a function of collector current; typical values

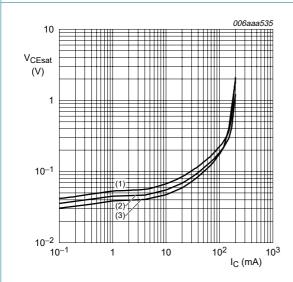


 $I_{\rm C}/I_{\rm B} = 20$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

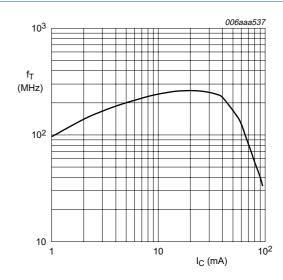
Fig 6. Per transistor: Base-emitter saturation voltage as a function of collector current; typical values



 $I_C/I_B = 20$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 7. Per transistor: Collector-emitter saturation voltage as a function of collector current; typical values



 V_{CE} = 5 V; T_{amb} = 25 °C

Fig 8. Per transistor: Transition frequency as a function of collector current; typical values

65 V, 100 mA NPN/NPN general-purpose transistor

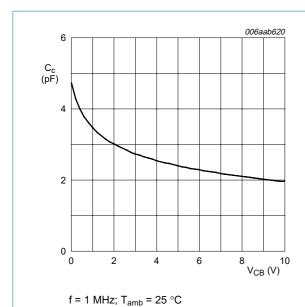
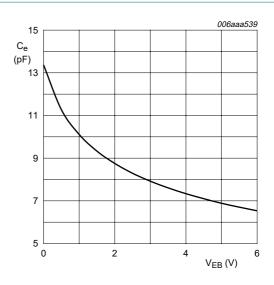


Fig 9. Per transistor: Collector capacitance as a function of collector-base voltage; typical values



 $f = 1 \text{ MHz}; T_{amb} = 25 \,^{\circ}\text{C}$

Fig 10. Per transistor: Emitter capacitance as a function of emitter-base voltage; typical values

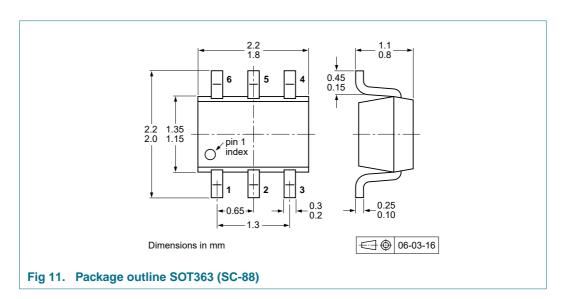
65 V, 100 mA NPN/NPN general-purpose transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline

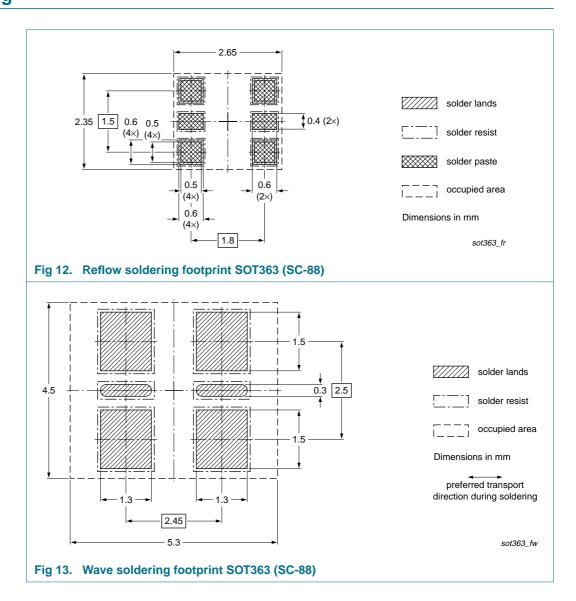


10. Packing information

Please refer to packing information on www.nexperia.com.

65 V, 100 mA NPN/NPN general-purpose transistor

11. Soldering



65 V, 100 mA NPN/NPN general-purpose transistor

12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BC846BS	20090824	Product data sheet	-	-

65 V, 100 mA NPN/NPN general-purpose transistor

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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65 V, 100 mA NPN/NPN general-purpose transistor

14. Contents

1	Product profile
1.1	General description
1.2	Features
1.3	Applications
1.4	Quick reference data 1
2	Pinning information 2
3	Ordering information
4	Marking 2
5	Limiting values 2
6	Thermal characteristics 3
7	Characteristics 4
8	Test information
8.1	Quality information
9	Package outline 8
10	Packing information 8
11	Soldering 9
12	Revision history
13	Legal information
13.1	Data sheet status
13.2	Definitions
13.3	Disclaimers
13.4	Trademarks11
14	Contents

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Dat

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